

### ADB18PS

## Application Specific Discretes A.S.D. $^{TM}$

# AUTOPROTECTED DIODE BRIDGE

#### **MAIN APPLICATIONS**

Any electronic equipment needing a diode bridge and protection against transient overvoltage:

- Caller Id
- Handset

#### **DESCRIPTION**

The ADB18PS combines a diode bridge and a clamping protection function.

Integrated monolithically within a SMD package, this device allows space saving and greater reliability.

It provides both rectification and protection for low power equipment directly supplied by mains.

#### **FEATURES**

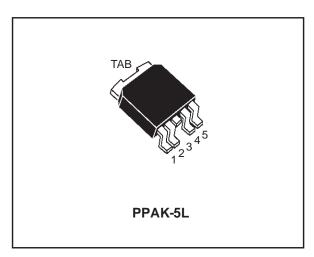
■ Peak pulse power dissipation 100 W (8/20 µs)

Stand-offvoltage: 18 VMaximum DC current: 0.5 A

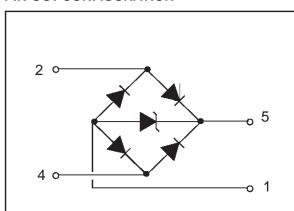
■ Clamping voltage: V<sub>CL</sub> < 50 V (8/20 µs)

#### **BENEFITS**

- Protection combined with rectification
- High reliability confered by monolithic construction
- Space saving
- Cost effective solution



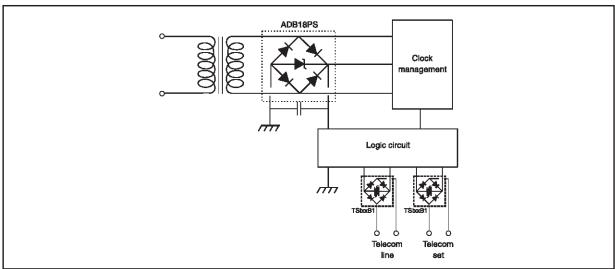
#### **PIN-OUT CONFIGURATION**



Pin	Description		
1	DC output		
2	AC input		
3	Not accessible		
4	AC input		
5	DC output		
TAB	Not to be connected		

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#### **APPLICATION CIRCUIT: Caller Id interface**



ABSOLUTE MAXIMUM RATINGS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
P <sub>PP</sub>	Peak pulse power dissipation (one pulse)	8 / 20 μs	100	W
Р	Power dissipation	T <sub>case</sub> = 70 °C	20	W
V <sub>RRM</sub>	Repetitive peak reverse voltage		18	V
I <sub>PP</sub>	Peak pulse reverse current (one pulse)	8 / 20 μs	2	Α
lF	Forward current for one diode		0.5	Α
I <sub>FSM</sub>	Non repetitive surge peak forward current	$t_p = 8.3 \text{ms}$ $t_p = 10 \text{ms}$	8 7.5	А
T <sub>stg</sub>	Storage temperature range		-40 to 150	°C
Tj	Maximum junction temperature		150	°C

#### **ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25$ °C).

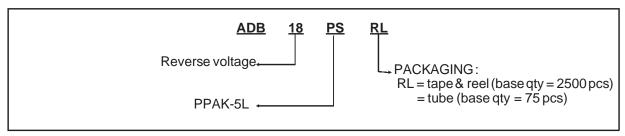
Symbol	Parameter	Test conditions	Тур	Max	Unit
V <sub>CL</sub>	Clamping voltage IPP = 2 A	8 / 20 μs		50	V
I <sub>RM</sub>	Leakage current	V <sub>RM</sub> = 18 V		2	μΑ
VF	Forward voltage for one diode	I <sub>F</sub> = 500 mA		1.4	V
С	Capacitance	$V_R = 0 V, F = 1 MHz$	50		pF

#### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-a)</sub>	Junction to ambient on FR4 (0.5 cm <sup>2</sup> )	80	°C/W
R <sub>th(j-a)</sub>	Junction to ambient on IMS (17 cm <sup>2</sup> )	30	°C/W
R <sub>th(j-c)</sub>	Junction to case	4	°C/W



#### **ORDER CODE**

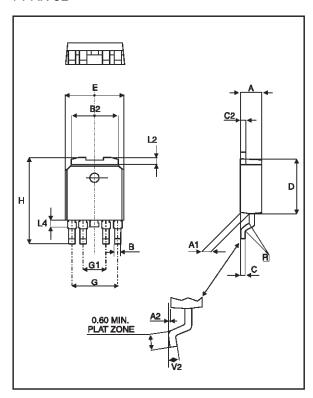


#### **MARKING**

Package	Туре	Marking	
PPAK-5L	ADB18PS	ADB18	

#### PACKAGE MECHANICAL DATA

PPAK-5L



	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max	Min.	Тур.	Max.
Α	2.20		2.40	0.0866		0.0945
A1	0.90		1.10	0.0354		0.0433
A2	0.03		0.23	0.0001		0.0009
В	0.4		0.90	0.0157		0.0236
B2	5.20		5.40	0.2047		0.2126
С	0.45		0.60	0.0177		0.0236
C2	0.48		0.60	0.0188		0.0236
D	6.00		6.20	0.2362		0.2441
E	6.40		6.60	0.2519		0.2598
G	4.9		5.25	0.1929		0.2067
G1	2.38		2.7	0.0937		0.1063
Н	9.35		10.10	0.369		0.3977
L2		0.80	1.00		0.0314	0.0393
L4	0.60		1.00	0.0236		0.0393
R		0.2			0.0078	
V2	0°		8°	0°		8°

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